

## 16K x 4 Static RAM

### Features

- High speed
  - 15 ns
- Output enable ( $\overline{OE}$ ) feature (7C166)
- CMOS for optimum speed/power
- Low active power
  - 633 mW
- Low standby power
  - 220 mW
- TTL-compatible inputs and outputs
- Automatic power-down when deselected

### Functional Description

The CY7C164 and CY7C166 are high-performance CMOS static RAMs organized as 16,384 by 4 bits. Easy memory expansion is provided by an active LOW chip enable ( $\overline{CE}$ ) and

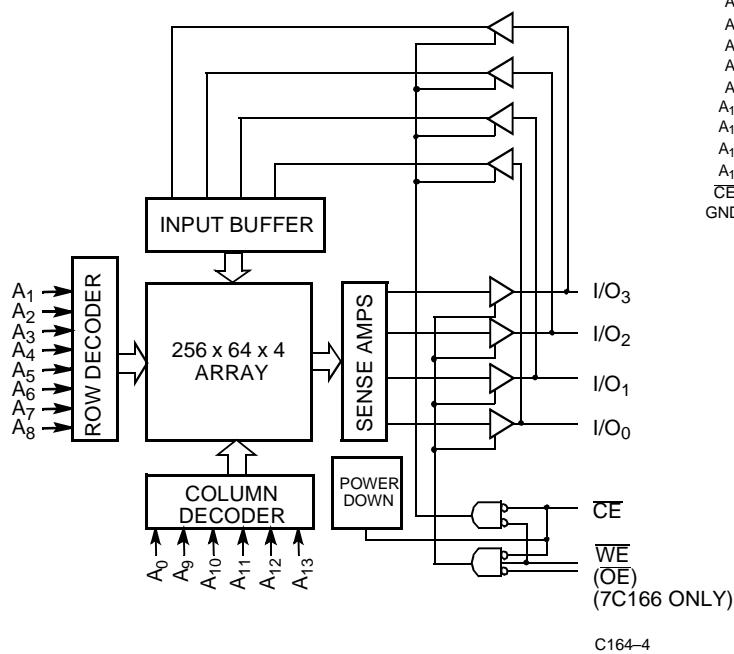
three-state drivers. The CY7C166 has an active low output enable ( $\overline{OE}$ ) feature. Both devices have an automatic power-down feature, reducing the power consumption by 65% when deselected.

Writing to the device is accomplished when the chip enable ( $\overline{CE}$ ) and write enable ( $\overline{WE}$ ) inputs are both LOW (and the output enable ( $\overline{OE}$ ) is LOW for the 7C166). Data on the four input/output pins (I/O0 through I/O3) is written into the memory location specified on the address pins (A0 through A13).

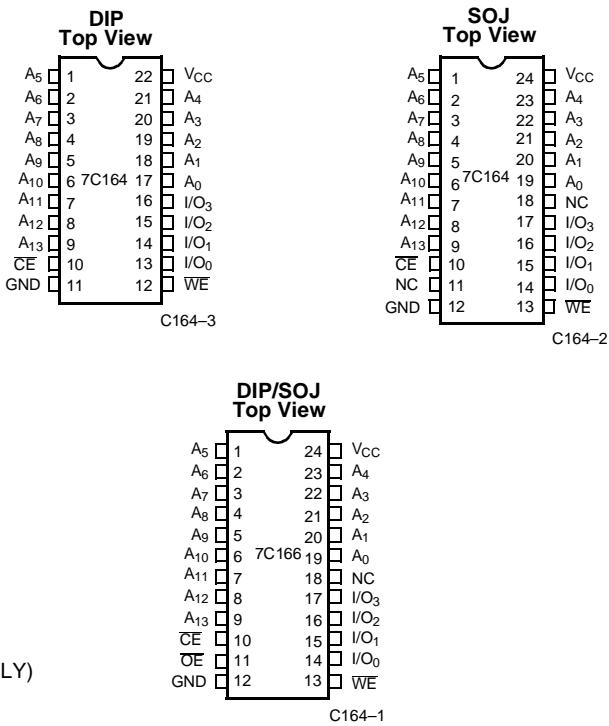
Reading the device is accomplished by taking chip enable ( $\overline{CE}$ ) LOW (and  $\overline{OE}$  LOW for 7C166), while write enable ( $\overline{WE}$ ) remains HIGH. Under these conditions the contents of the memory location specified on the address pins will appear on the four data I/O pins.

The I/O pins stay in a high-impedance state when chip enable ( $\overline{CE}$ ) is HIGH (or output enable ( $\overline{OE}$ ) is HIGH for 7C166). A die coat is used to insure alpha immunity.

### Logic Block Diagram



### Pin Configurations



### Selection Guide<sup>[1]</sup>

	7C164-12 7C166-12	7C164-15 7C166-15	7C164-20 7C166-20	7C164-25 7C166-25	7C164-35 7C166-35
Maximum Access Time (ns)	12	15	20	25	35
Maximum Operating Current (mA)	160	115	80	70	70
Maximum Standby Current (mA)	40/20	40/20	40/20	20/20	20/20

Shaded area contains advanced information.

**Note:**

1. For military specifications, see the CY6C164A/CY7C166A datasheet

## Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....  $-65^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$

Ambient Temperature with

Power Applied .....  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$

Supply Voltage to Ground Potential .....  $-0.5\text{V}$  to  $+7.0\text{V}$

DC Voltage Applied to Outputs  
in High Z State<sup>[2]</sup> .....  $-0.5\text{V}$  to  $+7.0\text{V}$

DC Input Voltage<sup>[2]</sup> .....  $-0.5\text{V}$  to  $+7.0\text{V}$

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage .....  $>2001\text{V}$   
(per MIL-STD-883, Method 3015)

Latch-Up Current .....  $>200\text{ mA}$

## Operating Range

Range	Ambient Temperature	$V_{CC}$
Commercial	$0^{\circ}\text{C}$ to $+70^{\circ}\text{C}$	$5\text{V} \pm 10\%$

## Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	7C164-12 7C166-12		7C164-15 7C166-15		7C164-20 7C166-20		7C164-25, 35 7C166-25, 35		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
$V_{OH}$	Output HIGH Voltage	$V_{CC} = \text{Min.}$ , $I_{OH} = -4.0\text{ mA}$	2.4		2.4		2.4		2.4		V
$V_{OL}$	Output LOW Voltage	$V_{CC} = \text{Min.}$ , $I_{OL} = 8.0\text{ mA}$		0.4		0.4		0.4		0.4	V
$V_{IH}$	Input HIGH Voltage		2.2	$V_{CC}$	2.2	$V_{CC}$	2.2	$V_{CC}$	2.2	$V_{CC}$	V
$V_{IL}$	Input LOW Voltage <sup>[2]</sup>		-0.5	0.8	-0.5	0.8	-0.5	0.8	-0.5	0.8	V
$I_{IX}$	Input Load Current	$\text{GND} \leq V_I \leq V_{CC}$	-5	+5	-5	+5	-5	+5	-5	+5	$\mu\text{A}$
$I_{OZ}$	Output Leakage Current	$\text{GND} \leq V_O \leq V_{CC}$ , Output Disabled	-5	+5	-5	+5	-5	+5	-5	+5	$\mu\text{A}$
$I_{OS}$	Output Short Circuit Current <sup>[3]</sup>	$V_{CC} = \text{Max.}$ , $V_{OUT} = \text{GND}$		-350		-350		-350		-350	mA
$I_{CC}$	$V_{CC}$ Operating Supply Current	$V_{CC} = \text{Max.}$ , $I_{OUT} = 0\text{ mA}$		160		115		80		70	mA
$I_{SB1}$	Automatic $\overline{CE}$ Power-Down Current <sup>[4]</sup>	$\text{Max. } V_{CC}, \overline{CE} \geq V_{IH}$ , Min. Duty Cycle = 100%		40		40		40		20	mA
$I_{SB2}$	Automatic $\overline{CE}$ Power-Down Current <sup>[4]</sup>	$\text{Max. } V_{CC},$ $\overline{CE} \geq V_{CC} - 0.3\text{V}$ , $V_{IN} \geq V_{CC} - 0.3\text{V}$ or $V_{IN} \leq 0.3\text{V}$		20		20		20		20	mA

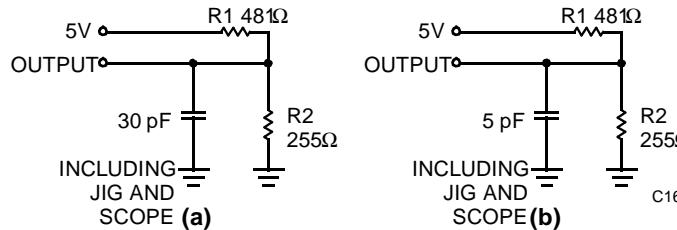
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## Capacitance<sup>[5]</sup>

Parameter	Description	Test Conditions	Max.	Unit
$C_{IN}$	Input Capacitance	$T_A = 25^{\circ}\text{C}$ , $f = 1\text{ MHz}$ , $V_{CC} = 5.0\text{V}$	10	pF
$C_{OUT}$	Output Capacitance		10	pF

**Notes:**

2. Minimum voltage is equal to  $-3.0\text{V}$  for pulse durations less than 30 ns.
3. Not more than 1 output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
4. A pull-up resistor to  $V_{CC}$  on the  $\overline{CE}$  input is required to keep the device deselected during  $V_{CC}$  power-up, otherwise  $I_{SB}$  will exceed values given.
5. Tested initially and after any design or process changes that may affect these parameters.

**AC Test Loads and Waveforms**


Equivalent to: THÉVENIN EQUIVALENT


**Switching Characteristics** Over the Operating Range<sup>[6]</sup>

Parameter	Description	7C164-12 7C166-12		7C164-15 7C166-15		7C164-20 7C166-20		7C164-25 7C166-25		7C164-35 7C166-35		Unit	
		Min.	Max.										
<b>READ CYCLE</b>													
$t_{RC}$	Read Cycle Time	12		15		20		25		35		ns	
$t_{AA}$	Address to Data Valid		12		15		20		25		35	ns	
$t_{OHA}$	Output Hold from Address Change	3		3		5		5		5		ns	
$t_{ACE}$	$\overline{CE}$ LOW to Data Valid		12		15		20		25		35	ns	
$t_{DOE}$	$\overline{OE}$ LOW to Data Valid	7C166	6		10		10		12		15	ns	
$t_{LZOE}$	$\overline{OE}$ LOW to Low Z	7C166	0		3		3		3		3	ns	
$t_{HZOE}$	$\overline{OE}$ HIGH to High Z	7C166		7		8		8		10		12	ns
$t_{LZCE}$	$\overline{CE}$ LOW to Low Z <sup>[7]</sup>		3		3		5		5		5	ns	
$t_{HZCE}$	$\overline{CE}$ HIGH to High Z <sup>[7, 8]</sup>			7		8		8		10		15	ns
$t_{PU}$	CE LOW to Power-Up		0		0		0		0		0		ns
$t_{PD}$	CE HIGH to Power-Down			12		15		20		20		20	ns
<b>WRITE CYCLE</b> <sup>[9]</sup>													
$t_{WC}$	Write Cycle Time	12		15		20		20		25		ns	
$t_{SCE}$	CE LOW to Write End	8		12		15		20		25		ns	
$t_{AW}$	Address Set-Up to Write End	9		12		15		20		25		ns	
$t_{HA}$	Address Hold from Write End	0		0		0		0		0		ns	
$t_{SA}$	Address Set-Up to Write Start	0		0		0		0		0		ns	
$t_{PWE}$	WE Pulse Width	8		12		15		15		20		ns	
$t_{SD}$	Data Set-Up to Write End	6		10		10		10		15		ns	
$t_{HD}$	Data Hold from Write End	0		0		0		0		0		ns	
$t_{LZWE}$	WE HIGH to Low Z <sup>[7]</sup>		3		5		5		5		5	ns	
$t_{HZWE}$	WE LOW to High Z <sup>[7, 8]</sup>			6		7		7		7		10	ns

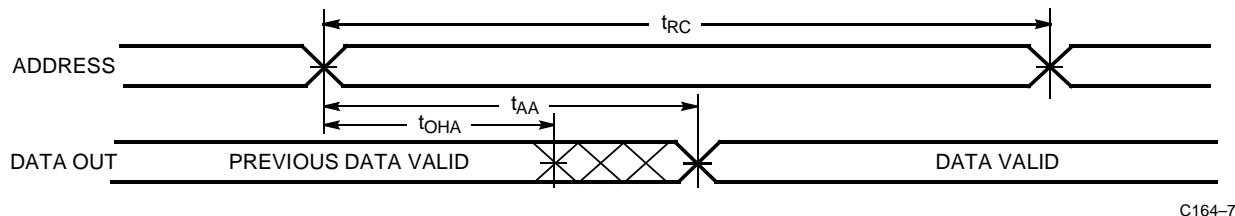
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**Notes:**

- Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified  $I_{OL}/I_{OH}$  and 30-pF load capacitance.
- At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$  for any given device. These parameters are guaranteed by design and not 100% tested.
- $t_{HZCE}$  and  $t_{HZWE}$  are specified with  $C_L = 5$  pF as in part (b) in AC Test Loads. Transition is measured  $\pm 500$  mV from steady-state voltage.
- The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

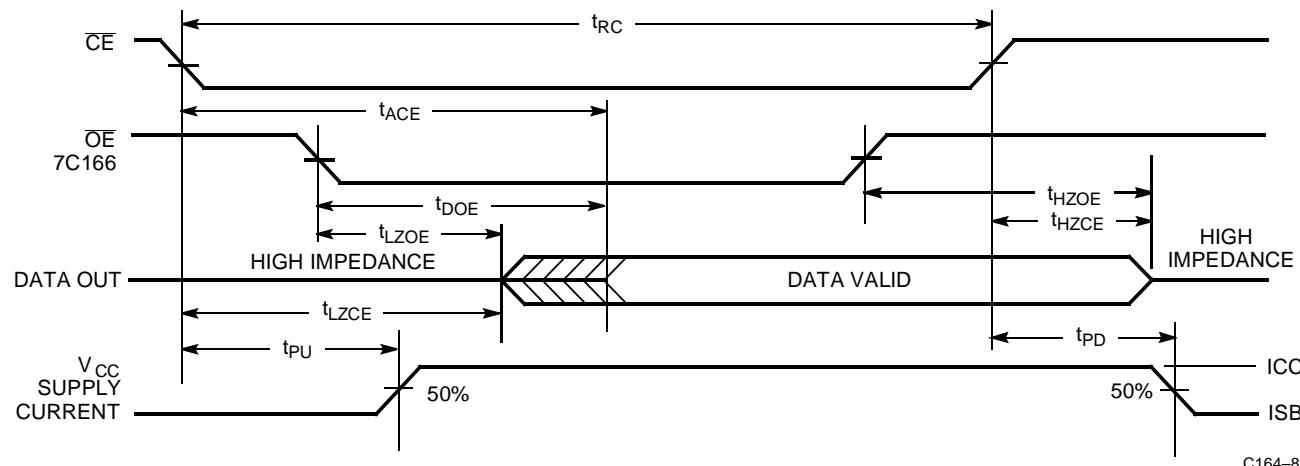
## Switching Waveforms

**ReadCycle No.1** [10,11]



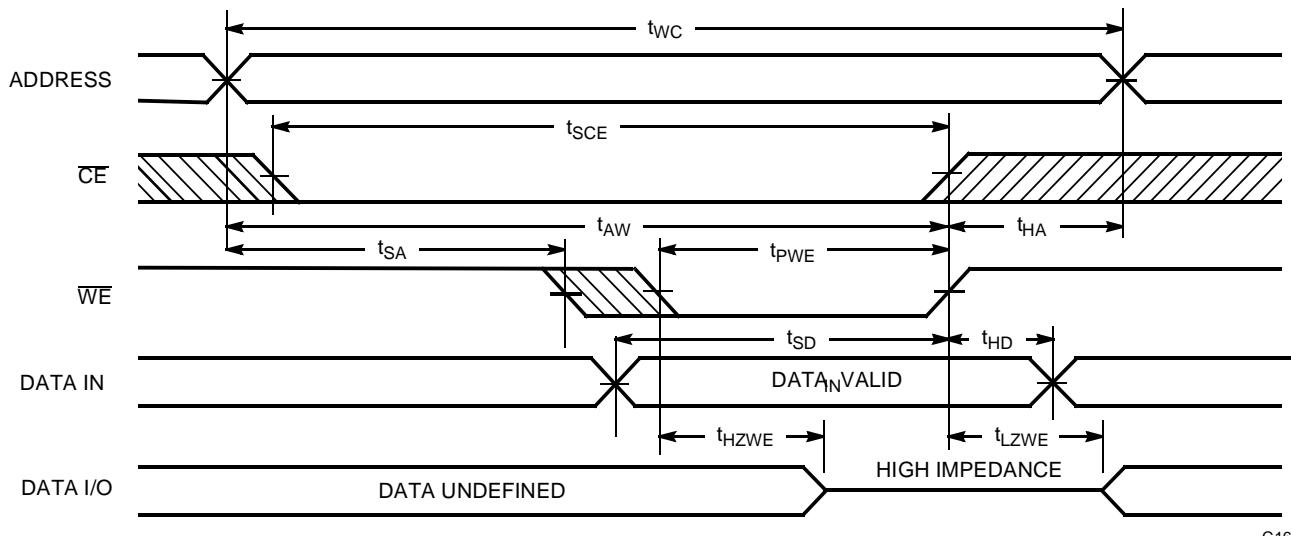
C164-7

**Read Cycle No.2** [10,12]



C164-8

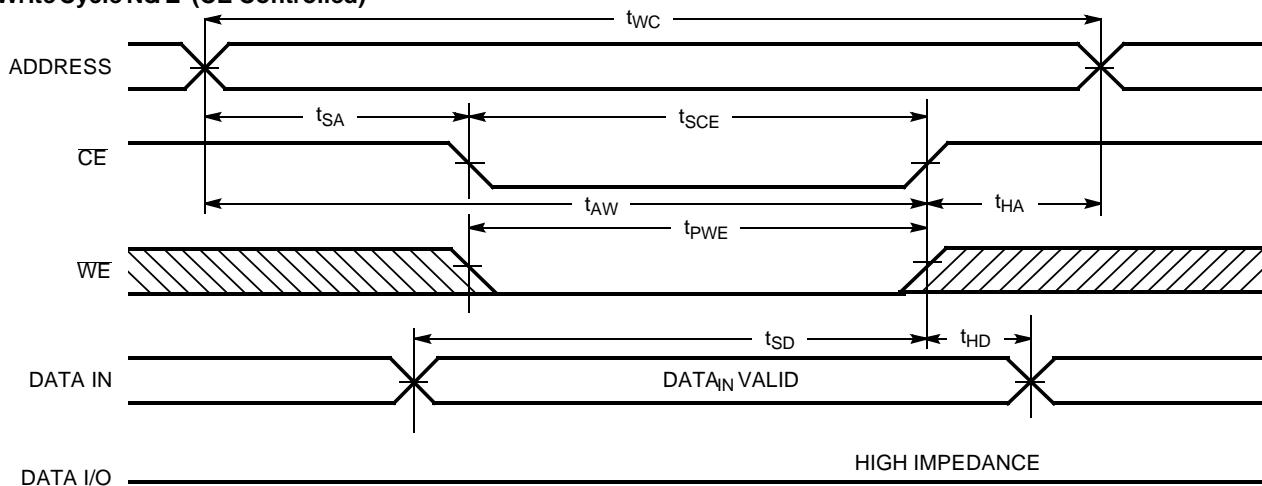
**Write Cycle No. 1 (WE Controlled)** [9,13]



C164-9

**Notes:**

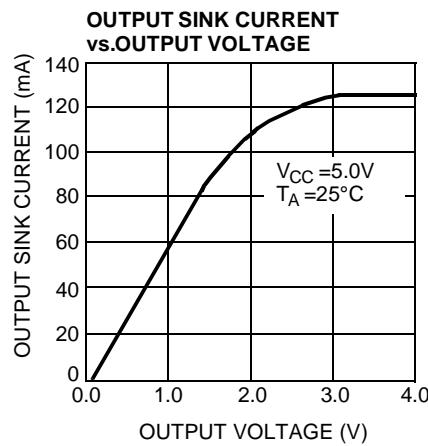
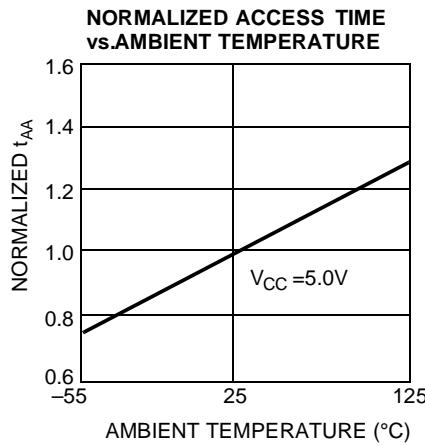
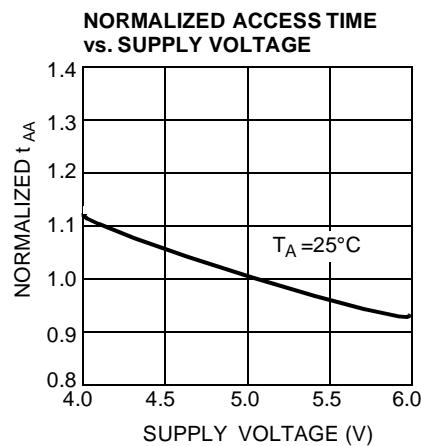
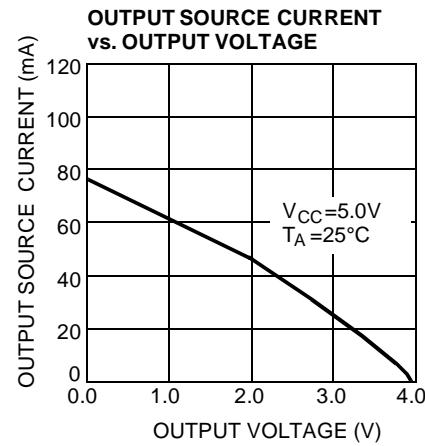
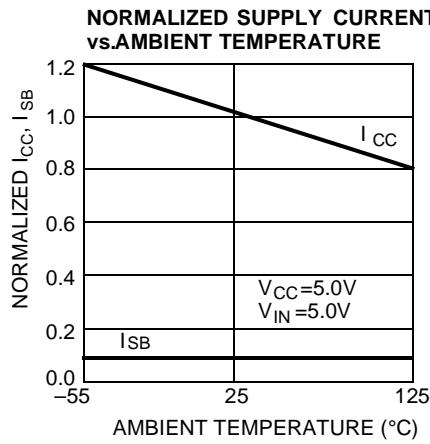
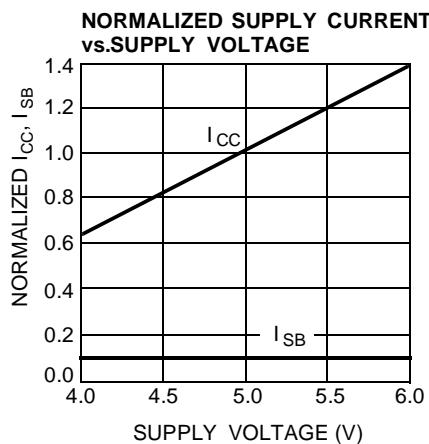
10.  $\overline{WE}$  is HIGH for read cycle.
11. Device is continuously selected,  $\overline{CE} = V_{IL}$ . (7C166:  $\overline{OE} = V_{IL}$  also).
12. Address valid prior to or coincident with  $\overline{CE}$  transition LOW.
13. 7C166 only: Data I/O will be high impedance if  $\overline{OE} = V_{IH}$ .

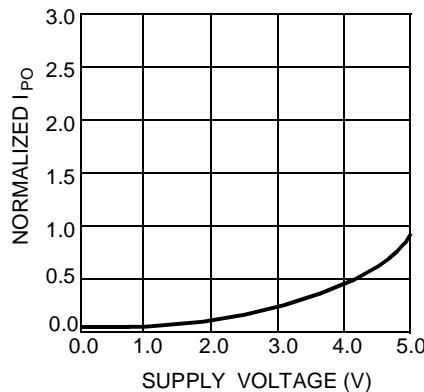
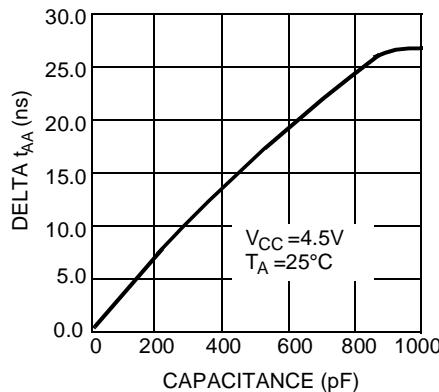
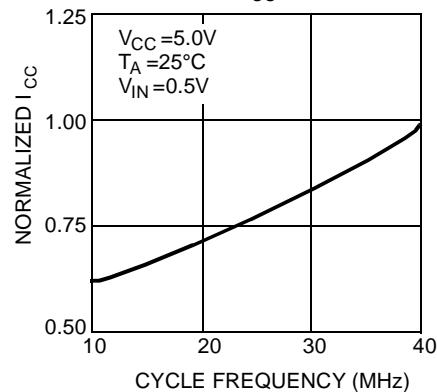
**Switching Waveforms (continued)**
**Write Cycle No. 2 (CE Controlled) [9,13,14]**


C164-10

**Note:**

 14. If CE goes HIGH simultaneously with WE HIGH, the output remains in a high-impedance state.

**Typical DC and AC Characteristics**


**Typical DC and AC Characteristics (continued)**
**TYPICAL POWER-ON CURRENT  
vs. SUPPLY VOLTAGE**

**TYPICAL ACCESS TIME CHANGE  
vs. OUTPUT LOADING**

**NORMALIZED  $I_{CC}$  vs. CYCLE TIME**

**CY7C164 Truth Table**

CE	WE	Input/Output	Mode
H	X	High Z	Deselect/Power-Down
L	H	Data Out	Read
L	L	Data In	Write

**CY7C166 Truth Table**

CE	WE	OE	Input/Output	Mode
H	X	X	High Z	Deselect/Power-Down
L	H	L	Data Out	Read
L	L	H	Data In	Write
L	H	H	High Z	Write

**Address Designators**

Address Name	Address Function	CY 7C164 Pin Number	CY7C166 Pin Number
A5	X3	1	1
A6	X4	2	2
A7	X5	3	3
A8	X6	4	4
A9	X7	5	5
A10	Y5	6	6
A11	Y4	7	7
A12	Y0	8	8
A13	Y1	9	9
A0	Y2	17	19
A1	Y3	18	20
A2	X0	19	21
A3	X1	20	22
A4	X2	21	23

**Ordering Information**

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
12	CY7C164-12PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C164-12VC	V13	24-Lead Molded SOJ	
15	CY7C164-15PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C164-15VC	V13	24-Lead Molded SOJ	
20	CY7C164-20PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C164-20VC	V13	24-Lead Molded SOJ	
25	CY7C164-25PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C164-25VC	V13	24-Lead Molded SOJ	
35	CY7C164-35PC	P9	22-Lead (300-Mil) Molded DIP	Commercial
	CY7C164-35VC	V13	24-Lead Molded SOJ	

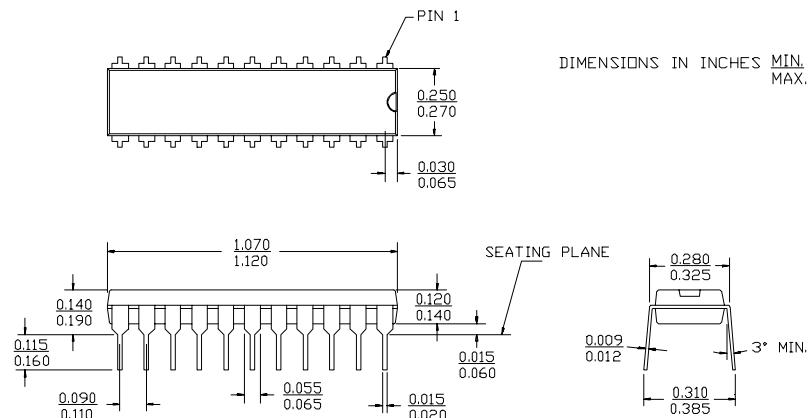
Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
12	CY7C166-12PC	P13	24-Lead (300-Mil) Molded DIP	Commercial
	CY7C166-12VC	V13	24-Lead Molded SOJ	
15	CY7C166-15PC	P13	24-Lead (300-Mil) Molded DIP	Commercial
	CY7C166-15VC	V13	24-Lead Molded SOJ	
20	CY7C166-20PC	P13	24-Lead (300-Mil) Molded DIP	Commercial
	CY7C166-20VC	V13	24-Lead Molded SOJ	
25	CY7C166-25PC	P13	24-Lead (300-Mil) Molded DIP	Commercial
	CY7C166-25VC	V13	24-Lead Molded SOJ	
35	CY7C166-35PC	P13	24-Lead (300-Mil) Molded DIP	Commercial
	CY7C166-35VC	V13	24-Lead Molded SOJ	

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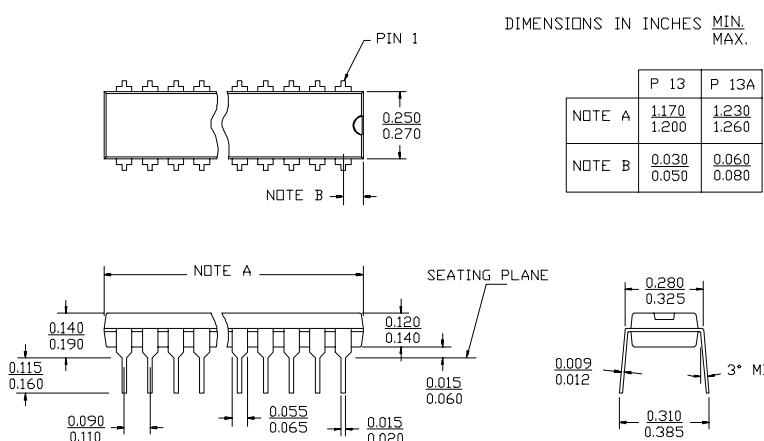
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## Package Diagrams

### 22-Lead (300-Mil) Molded DIP P9



### 24-Lead (300-Mil) Molded DIP P13/P13A



### 24-Lead Molded SOJ V13

